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Atty Docket No.  
OPE-007

Serial No.  
10/689,019

Applicant  
Geoff W. Taylor

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October 20, 2003

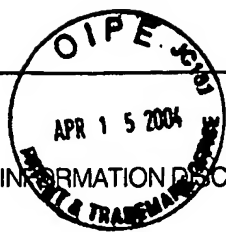
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US PATENT DOCUMENTS

Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing date if approp.
SR	A	6,479,844	11/12/02	Taylor	257	192	
	B	2002/0067877A1	06/06/02	Braun	385	15	
	C	6,351,001	02/26/02	Stevens et al.	257	223	
	D	2001/0043629	11/2001	Sun et al.	372	43	
	E	5,698,900	12/16/97	Bozada et al.	257	744	
	F	4,683,484	07/28/97	Derkits, Jr.	357	16	
	G	5,517,244	05/14/96	Stekelenburg et al.	348	305	
	H	5,436,759	07/25/95	Dijaili et al.	359	333	
	I	5,422,501	06/06/95	Bayraktaroglu	257	195	
	J	5,386,128	01/95	Fossum et al.	257	183.1	
	K	5,337,328	08/09/94	Lang et al.	372	45	
	L	5,202,896	04/13/93	Taylor	372	50	
	M	5,105,248	04/14/92	Burke, et al.	357	24	
	N	5,010,374	04/23/91	Cooke et al.	357	16	
	O	4,995,061	02/19/91	Hynecek	377	58	
	P	4,949,350	08/14/90	Jewell et al.	372	45	
	Q	4,899,200	02/06/90	Shur et al.	357	30	
	R	4,829,272	05/09/89	Kameya	333	139	
	S	4,827,320	05/02/89	Markoc et al.	357	22	
	T	4,814,774	03/21/89	Herczfeld	432	372	
	U	4,806,997	02/21/89	Simmons et al.	357	16	
	V	4,658,403	04/14/87	Takiguchi et al.	372	96	
SR	W	4,584,697	04/22/86	Hazendonk et al.	377	60	

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SR	A	4,424,535	01/03/84	Mimura	257	217	
	B	4,229,752	10/21/80	Hynecek	357	24	
	C	3,919,656	11/11/75	Sokal et al.	330	51	
	D	6,031,243	02/29/00	Taylor	257	192	
	E	5,422,501	06/06/95	Bayraktaroglu	257	744	
SR	F	5,698,900	12/16/97	Bozada et al.	257	13	
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SR	A	PCT/US02/06802	09/12/02	Taylor			
SR	B	PCT/US03/13183	10/29/03	Taylor			
	C						
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